

1. Material Substrate GaP (N Type)
Epitaxial Layer GaAsP (P/N Type)

2. Electrode N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.6		V	IF=1mA
	$V_{F(2)}$			2.2	V	IF=20mA
Reverse Voltage	V_R	8			V	IR=10uA
Brightness	Iv	200	300		mcd	IF=20mA
Wavelength	λ_d		618		nm	IF=20mA
	$\Delta\lambda$		40		nm	IF=20mA

※ Note : Brightness is measured by Sorter E/T system with bare chip.

4. Mechanical Data

- (a) Emission Area ----- 10mil x 10mil
- (b) Bottom Area ----- 11mil x 11mil
- (c) Bonding Pad ----- 115um
- (d) Chip Thickness ----- 11mil
- (e) Junction Height ----- 10.6mil

